

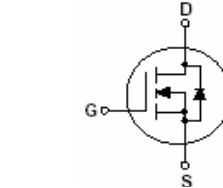
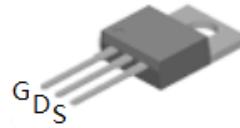

**Technology Int'l**

## WFP7N60

**600V N-Channel MOSFET**

### Features

- Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Extended Safe Operating Area
- Unrivalled Gate Charge : $Q_g = 40\text{nC}$  (Typ.)
- $BVDSS=600\text{V}, ID=7\text{A}$
- $R_{DS(on)} : 1.2 \Omega$  (Max) @ $VG=10\text{V}$
- 100% Avalanche Tested



TO-220

G-Gate,D-Drain,S-Source

### Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	WFP7N60	Units
$V_{DSS}$	Drain-Source Voltage	600	V
$I_D$	Drain Current -continuous ( $T_c=25^\circ\text{C}$ )	7	A
	-continuous ( $T_c=100^\circ\text{C}$ )	4.7	A
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Plused Avalanche Energy (Note1)	420	mJ
$I_{AR}$	Avalanche Current (Note2)	7	A
$P_D$	Power Dissipation ( $T_c=25^\circ\text{C}$ )	147	W
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 ~ +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case	--	0.88	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance,Case to Sink	0.5	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	--	62.5	$^\circ\text{C/W}$

**Electrical Characteristics** T<sub>c</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	ID=250 μA, VGS=0	600	--	--	V
△BV <sub>DSS</sub> / △T <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> =250 μA, Reference to 25°C	--	0.67	--	V/°C
IDSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> =600V, V <sub>Gs</sub> =0V	--	--	10	μA
		V <sub>DS</sub> =480V, T <sub>c</sub> =125°C			100	μA
IGSSF	Gate-body leakage Current, Forward	V <sub>Gs</sub> =+30V, V <sub>DS</sub> =0V	--	--	100	nA
IGSSR	Gate-body leakage Current, Reverse	V <sub>Gs</sub> =-30V, V <sub>DS</sub> =0V	--	--	-100	nA

**On Characteristics**

V <sub>GS(th)</sub>	Date Threshold Voltage	I <sub>d</sub> =250uA, V <sub>DS</sub> =V <sub>Gs</sub>	2	--	4	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	I <sub>d</sub> =3.7A, V <sub>Gs</sub> =10V	--	--	1.2	Ω

**Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>Gs</sub> =0, f=1.0MHz	--	1100	1430	pF
C <sub>oss</sub>	Output Capacitance		--	135	175	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	16	21	pF

**Switching Characteristics**

T <sub>d(on)</sub>	Turn-On Delay Time	VDD=300V, ID=7A RG=25Ω (Note 3,4)	--	30	70	nS
T <sub>r</sub>	Turn-On Rise Time		--	80	170	nS
T <sub>d(off)</sub>	Turn-Off Delay Time		--	65	140	nS
T <sub>f</sub>	Turn-Off Fall Time		--	60	130	nS
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =480, V <sub>Gs</sub> =10V, ID=7A (Note 3,4)	--	29	38	nC
Q <sub>gs</sub>	Gate-Source Charge		--	7	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	14.5	--	nC

**Drain-Source Diode Characteristics and Maximum Ratings**

I <sub>s</sub>	Maximum Continuous Drain-Source Diode Forward Current	--	--	7	A	
I <sub>SM</sub>	Maximum Plused Drain-Source Diode Forward Current	--	--	28	A	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	I <sub>d</sub> =7A	--	--	1.5	V
trr	Reverse Recovery Time	I <sub>s</sub> =7A, V <sub>Gs</sub> =0V di <sub>f</sub> /dt=100A/ μs (Note 3)	--	320	--	nS
Qrr	Reverse Recovery Charge		--	2.4	--	μC

\*Notes 1, L=15.7mH, IAS=7A, VDD=50V, RG=25Ω, Starting T<sub>J</sub>=25°C

2, Repetitive Rating : Pulse width limited by maximum junction temperature

3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

4, Essentially Independent of Operating Temperature

## Typical Characteristics

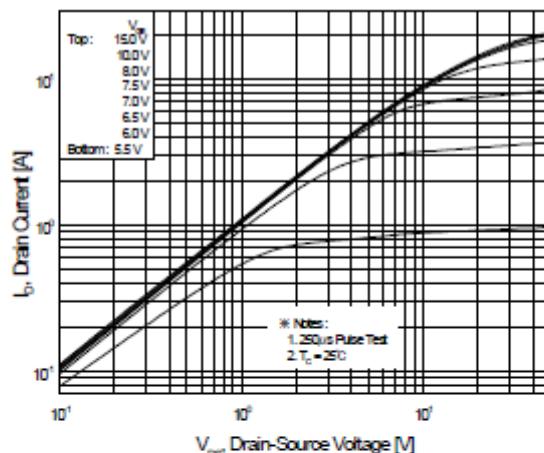


Figure 1. On-Region Characteristics

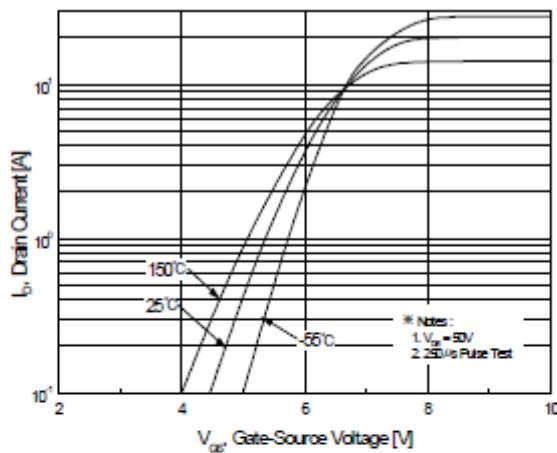


Figure 2. Transfer Characteristics

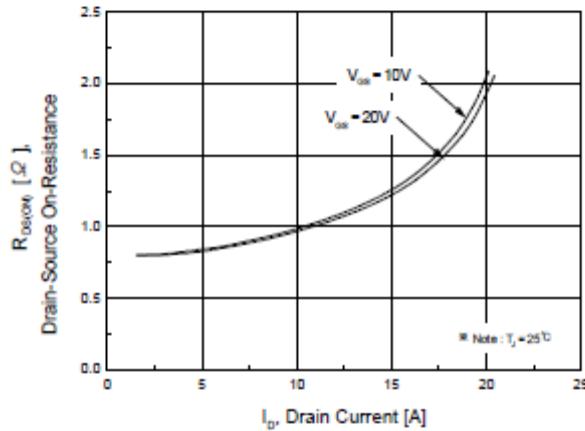


Figure 3. On-Resistance Variation vs.  
Drain Current and Gate Voltage

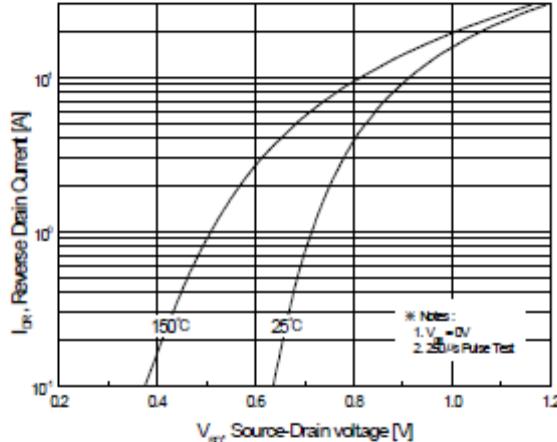


Figure 4. Body Diode Forward Voltage  
Variation vs. Source Current  
and Temperature

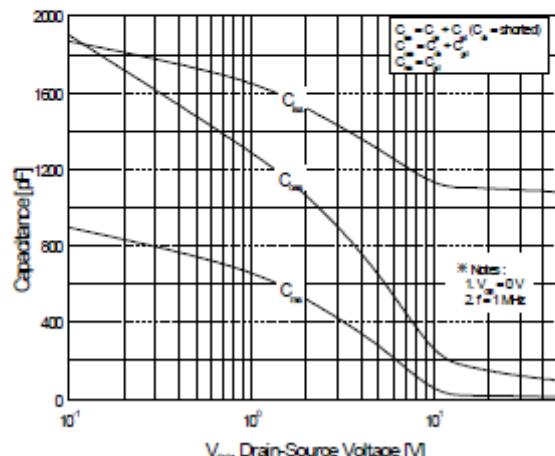


Figure 5. Capacitance Characteristics

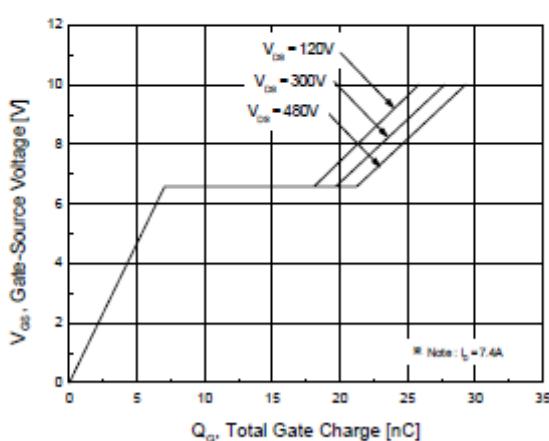


Figure 6. Gate Charge Characteristics

## Typical Characteristics (Continued)

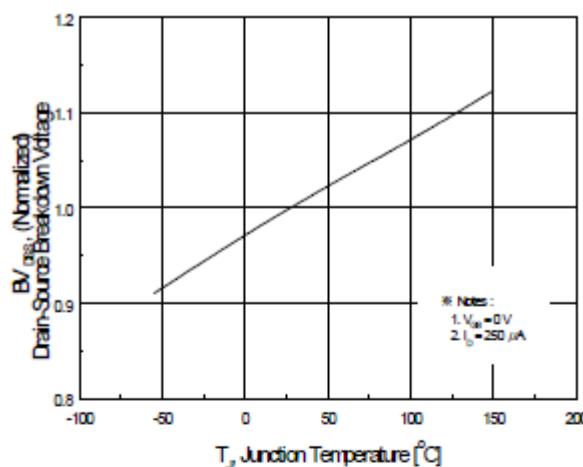


Figure 7. Breakdown Voltage Variation  
vs. Temperature

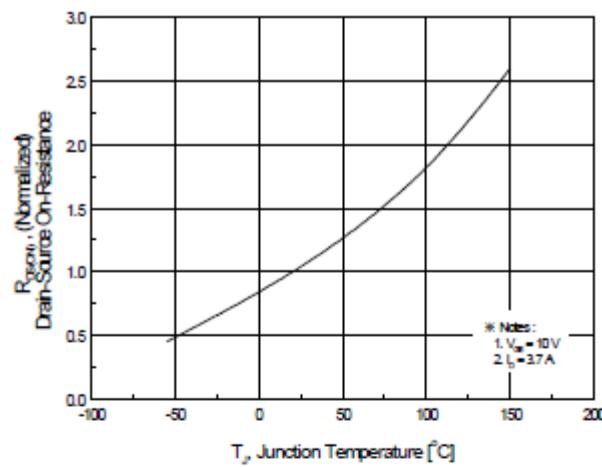


Figure 8. On-Resistance Variation  
vs. Temperature

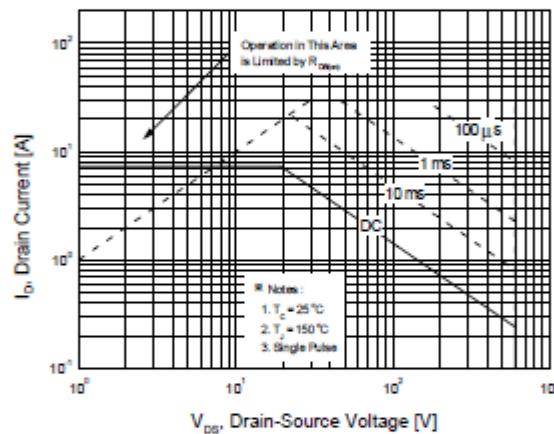


Figure 9. Maximum Safe Operating Area

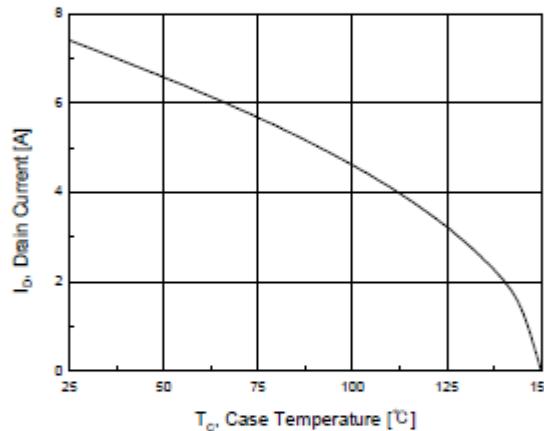


Figure 10. Maximum Drain Current  
vs. Case Temperature

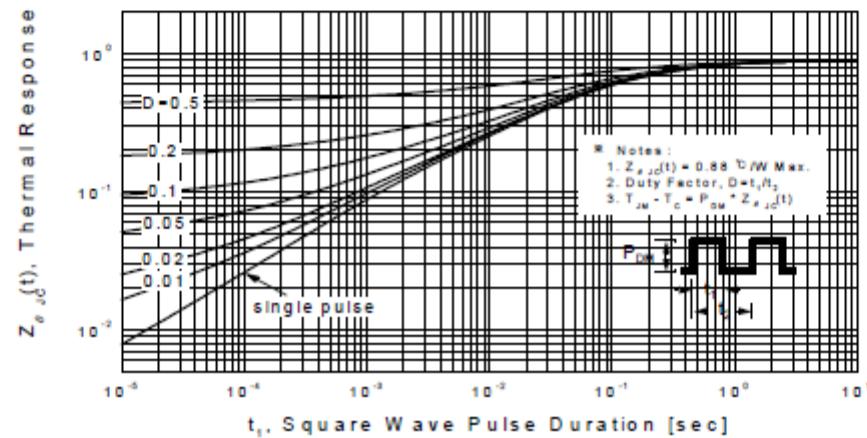
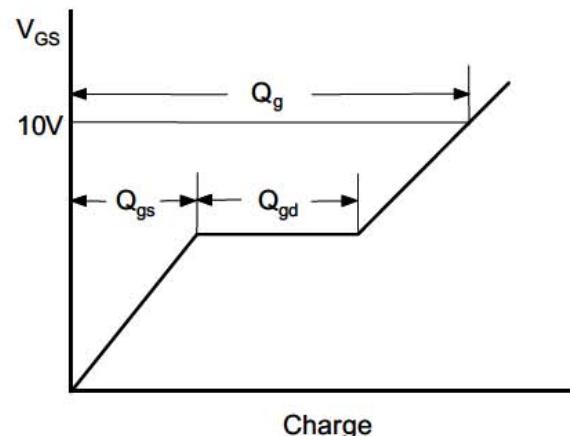
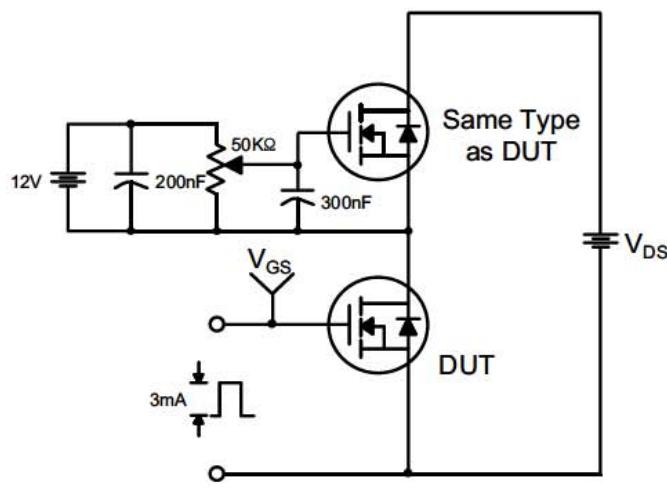
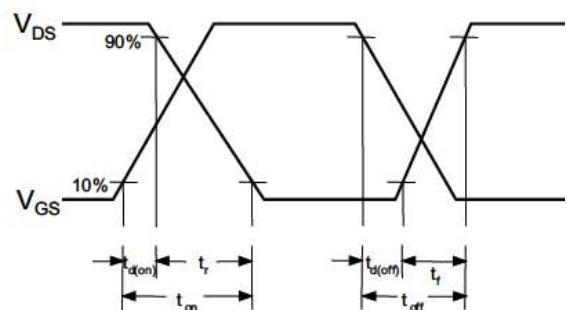
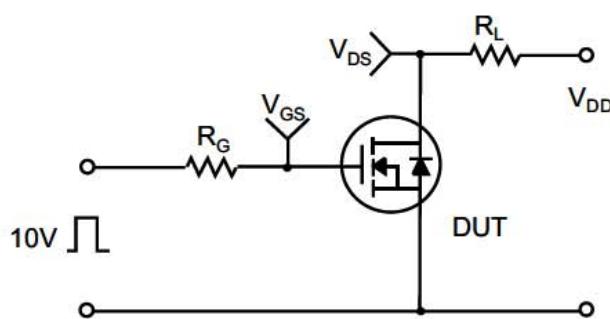
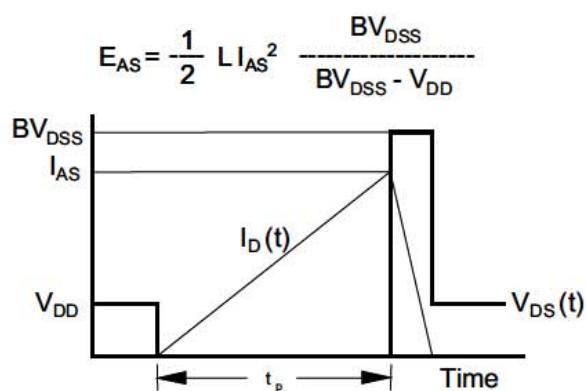
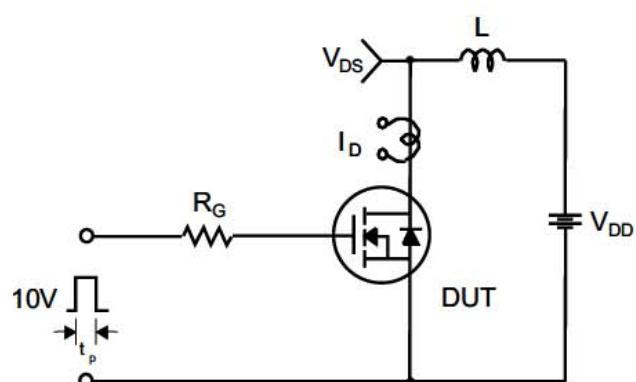


Figure 11. Transient Thermal Response Curve

**Gate Charge Test Circuit & Waveform**

**Resistive Switching Test Circuit & Waveforms**

**Unclamped Inductive Switching Test Circuit & Waveforms**


## Peak Diode Recovery dv/dt Test Circuit &amp; Waveforms

